

Description

The HXY2300MI uses advanced trench technology to provide excellent $R_{\text{DS(ON)}}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.



General Features

 $V_{DS} = 20V I_D = 6 A$

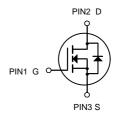
 $R_{DS(ON)}$ < 27m Ω @ V_{GS} =4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY2300MI	SOT23-3L	2300	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter		Limit	Unit	
V _{DS}	Drain-Source Voltage		20	V	
V _G s	Gate-Source Voltage		±12	V	
I _D	Continuous Drain Current	T _A =25℃	6	А	
		T _A =70°C	3.6		
Ірм	Drain Current-Pulsed (Note 1)		15	Α	
P _D	Maximum Power Dissipation		1.25	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)		100	°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	22.5	-	V
Zero Gate Voltage Drain Current	loss	V _{DS} =20V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.65	1.0	V
		V _{GS} =4.5V, I _D =4.0 A	-	22	27	mΩ
Drain-Source On-State Resistance	Rds(on)	V _{GS} =2.5V, I _D =4.5A	-	28	40	mΩ
Forward Transconductance	grs	V _{DS} =10V,I _D =4A	-	10	-	S
Input Capacitance	Clss	V _{DS} =8V,V _{GS} =0V,	-	500	-	PF
Output Capacitance	Coss		-	295	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	96	-	PF
Turn-on Delay Time	t d(on)	V _{DD} =10V,I _D =1A V _{GS} =4.5V,R _{GEN} =6Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	30	-	nS
Turn-Off Delay Time	td(off)		-	35	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =3A,V _{GS} =4.5V	-	10	15	nC
Gate-Source Charge	Qgs		-	2.3	-	nC
Gate-Drain Charge	Q _{gd}	1	-	2.9	-	nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	4.5	Α

Notes:

- 1. Repetitive rating: pulse width limited by maximum junction temperature.
- **2.** Surface mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

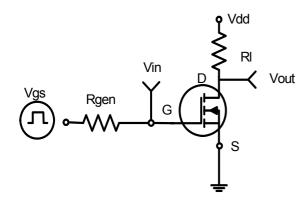


Figure 1:Switching Test Circuit

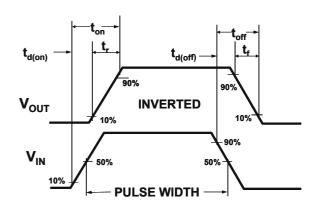


Figure 2:Switching Waveforms

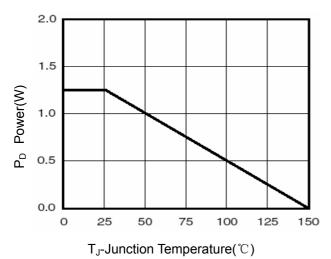


Figure 3 Power Dissipation

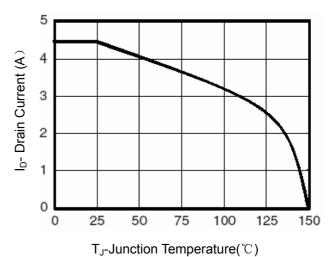


Figure 4 Drain Current

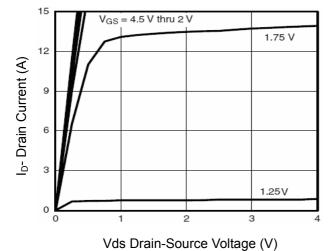


Figure 5 Output Characteristics

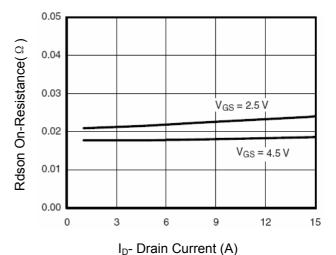


Figure 6 Drain-Source On-Resistance



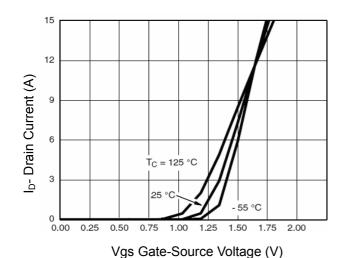
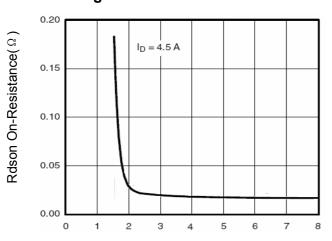


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs. Vgs

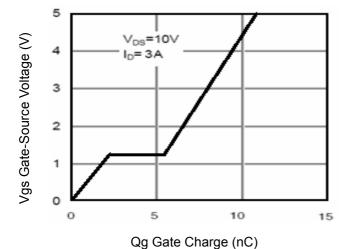


Figure 11 Gate Charge

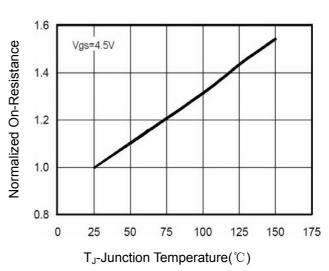


Figure 8 Drain-Source On-Resistance

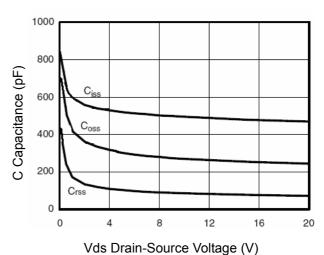
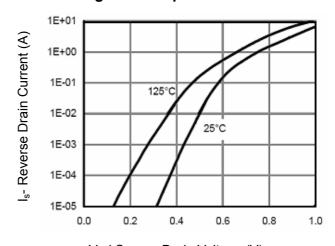


Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



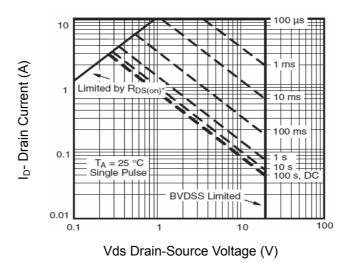


Figure 13 Safe Operation Area

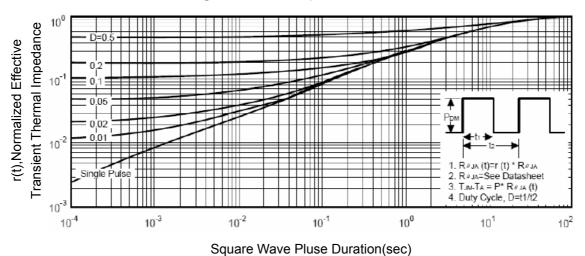
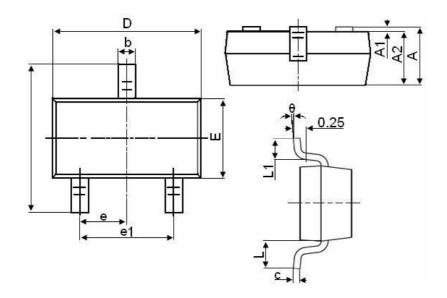


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	

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